

NCH75R260F

N-Channel Silicon Carbide MOSFET



Voltage: 750 Volts

Current: 10.0 Ampers

Package: TO-220FP

Features

- NH'S Advanced Silicon Carbide MOSFET Technology
- High Blocking Voltage And Low Capacitances
- High-Speed Switching For Very Low Switching Losses
- Excellent $Q_g \cdot R_{ds(on)}$ Product(FOM)

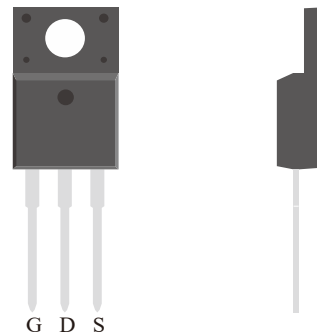
Typical Applications

- High Voltage DC/DC Converters
- Adaptor And Charger
- Battery Chargers And Motor Drives
- LED Drives And LED Lighting

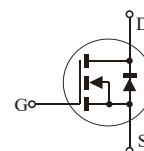
Product Summary

V _{DS} Min.@T _j	750	V
I _D Min.@T _a	10.0	A
R _{DS(ON)} (TYP)@18V,T _j =25°C	260	mΩ

Diagram:



Polarity:



*100% UIS TESTED

*100% ΔV_{DS} TESTED

Absolute Maximum Ratings (T_a=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Ratings	Unit
Drain-Source Voltage		V _{DS}	750	V
Gate-Source Voltage		V _{GS} MAX. V _{GS} O.P.	-10/+22 0/+15 or 18	V
Continuous Drain Current (Note 1)	T _a = 25 °C T _a = 100 °C	I _D	10.0 8.0	A
Drain Current-Pulse(Note 1)	T _j < 175 °C	I _{DM}	18	A
Maximum Power Dissipation Power	T _a = 25 °C	P _D	68	W
Dissipation Derating Factor Above 25°C	T _a = 100 °C		34	
Derating Factor		D _F	0.45	W/°C
Avalanche Current,Single Pulse (Note 1)	L= 0.5 mH	I _{AS}	8.2	A
Single Pulse Avalanche Energy (Note 1) Test Circuit & Waveform See Fig.22	L= 0.5 mH I _{AS} = 8.2 A,R _G = 10.0 Ω Starting T _j =25 °C,V _G = 18.0 V	E _{AS}	16.8	mJ

Thermal Characteristics (T_a=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Typ.	Unit
Junction Temperature		T _J	-55 to 175	°C
Storage Temperature Range		T _{STD}	-55 to 175	°C
Thermal Resistance Junction To Ambient With Steady-State	Still Air Environment With T _a =25°C	R _{θJA}	50	°C/W
Thermal Resistance Junction-Case With Steady-State	Device Mounted On 75mm x 45mm x 2.5mm Alu. Heat.	R _{θJC}	2.2	

Notes: 1.Pulse Width Limited By Max. Junction Temperature. (See Fig. 19).

NCH75R260F
N-Channel Silicon Carbide MOSFET

Electrical Characteristics (Ta=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Static Off Characteristics						
Drain-Source Breakdown Voltage	VGS=0V,ID=100uA	BV _{DSS}	750	--	--	V
Zero Gate Voltage Drain Current	VDS= 0 V,VGS=0V,Tj=25°C	I _{DSS}	--	0.1	20	uA
	VDS= 750 V,VGS=0V,Tj=175°C		--	3	--	
Gate To Source Leakage Current	VGS= 22 V,VDS=0V	I _{GSS}	--	--	250	nA
Source To Gate Leakage Current	VGS= -10 V,VDS=0V	I _{SGS}	--	--	250	nA
Forward Transconductance	ID= 4.0 A,VDS= 20 V	g _{fs}	--	2.9	--	S
Static On Characteristics						
Gate Threshold Voltage	VGS= VDS, ID=10mA ,Tj=25°C	V _{GS(th)}	3	3.7	5	V
	VGS= VDS, ID=10mA ,Tj=175°C		--	2.7	--	
Drain-Source On Resistance	ID= 4.0 A,VGS= 18.0 V,Tj=25°C	R _{DS(on)}	--	260	300	mΩ
	ID= 4.0 A,VGS= 18.0 V,Tj=175°C		--	302	330	
	ID= 4.0 A,VGS= 15.0 V,Tj=25°C		--	338	450	
	ID= 4.0 A,VGS= 15.0 V,Tj=175°C		--	365	486	
Dynamic Characteristics						
Input Capacitance	VDS= 650 V	C _{iss}	--	223	--	pF
Output Capacitance	VGS= 0 V	C _{oss}	--	22	--	pF
Reverse Transfer Capacitance	F= 1 MHZ	C _{rss}	--	3.5	--	pF
Gate Resistance	VGS=0V,VDS=0V,Freq.=1MHz	R _g	--	26	--	Ω
Switching Paramters (Test Circuit & Waveform See Fig.20)						
Turn-On Delay Time	VDS= 400 V ID= 4.0 A	Tj=25°C	--	11	--	ns
		Tj=175°C	--	10.5	--	
Turn-On Rise Time	VGS= 0/+18 V RG= 10.0 Ω	Tj=25°C	--	7.5	--	ns
		Tj=175°C	--	7.1	--	
Turn-Off Delay Time	L= 600 μH	Tj=25°C	--	8	--	ns
		Tj=175°C	--	7.6	--	
Turn-Off Rise Time		Tj=25°C	--	5	--	ns
		Tj=175°C	--	4.3	--	
Turn-On Switching Loss		Tj=25°C	--	14.8	--	μJ
		Tj=175°C	--	14.0	--	
Turn-Off Switching Loss		Tj=25°C	--	10.4	--	μJ
		Tj=175°C	--	9.5	--	
Total Switching Energy		Tj=25°C	--	25.1	--	μJ
		Tj=175°C	--	23.5	--	

NCH75R260F
N-Channel Silicon Carbide MOSFET

Electrical Characteristics (Ta=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Gate Charge Parameters (Test Circuit & Waveform See Fig.21)						
Total Gate Charge	VDS= 400 V	Q_g	--	9	--	nC
Gate-Source Charge	VGS= 0/+18 V	Q_{gs}	--	3.5	--	nC
Gate-Drain Charge	ID= 4.0 A	Q_{gd}	--	1.2	--	nC
Drain-Source Diode Characteristics And Maximum Ratings (Test Circuit & Waveform See Fig.23)						
Max. Diode Forward Current	Tj= 25 °C	I_s	--	--	10.0	A
tp Limited by Tj(max)	Tj= 100 °C		--	--	8.0	A
Max. Pulsed Forward Current		I_{SM}	--	--	15	A
Diode Forward Voltage	ID= 3.0 A, VGS=-0V Tj=25°C Tj=175°C	V_{SD}	--	3.5 3.0	--	V
Reverse Recovery Time	IS= 5.0 A di/dt= 1000.0 A/us Tj=25°C Tj=175°C	t_{rr}	--	9.2 10.4	--	ns
Reverse Recovery Charge	VGS= 0.0 V VDS= 400 V Tj=25°C Tj=175°C	Q_{rr}	--	25 28.8	--	nC
Reverse Recovery Current	Tj=25°C Tj=175°C	I_{rrm}	--	5.0 5.5	--	A
Reverse Recovery Energy	Tj=25°C Tj=175°C	E_{rr}	--	9.2 11.5	--	μJ

NCH75R260F

N-Channel Silicon Carbide MOSFET



Typical Characteristics Curves

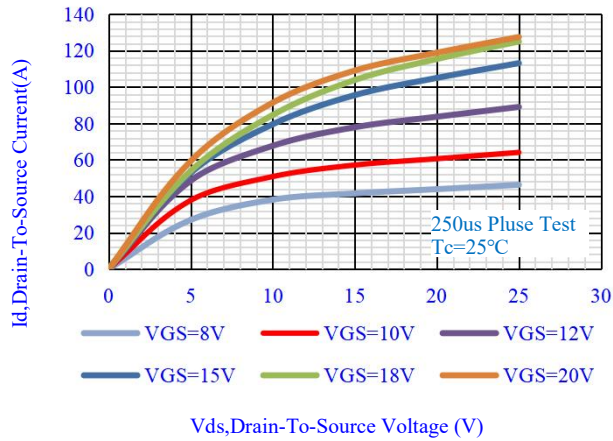


Fig.1-Output Characteristics@Tj=25°C

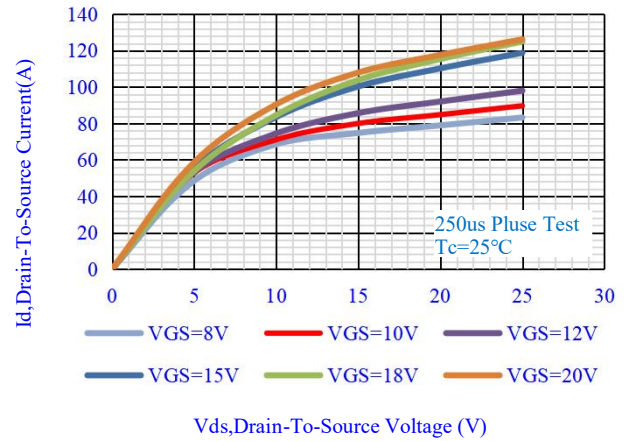


Fig.2-Output Characteristics@Tj=175°C

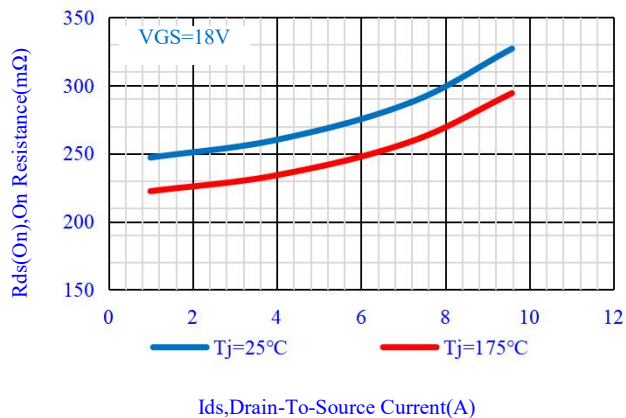


Fig.3-On Resistance Vs. Drain Current

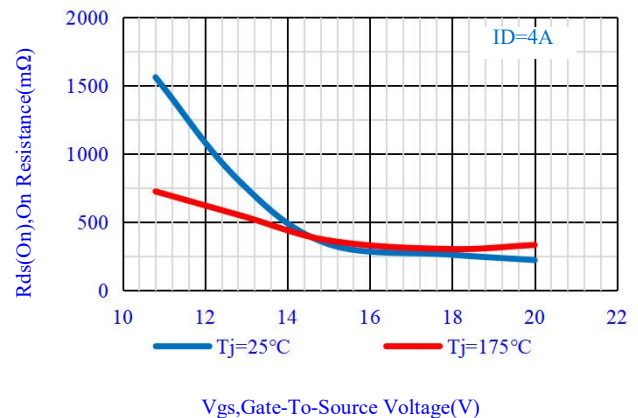


Fig.4-On Resistance Vs. Gate Source Voltage

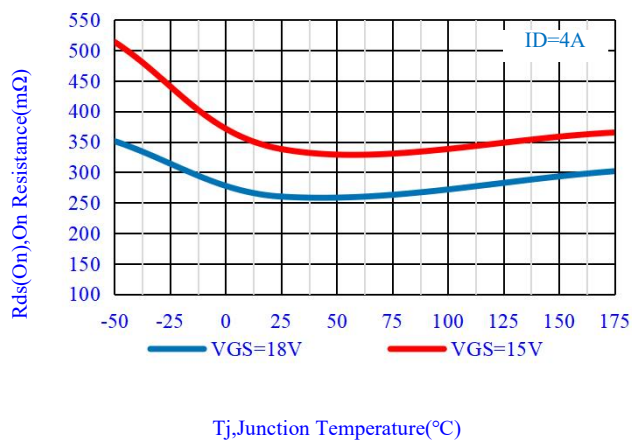


Fig.5-On Resistance Vs. Junction Temperature

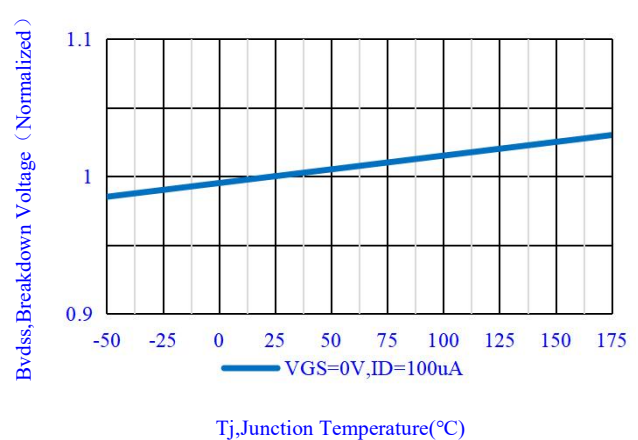


Fig.6-Breakdown Voltage Vs. Junction Temperature

NCH75R260F

N-Channel Silicon Carbide MOSFET



Typical Characteristics Curves

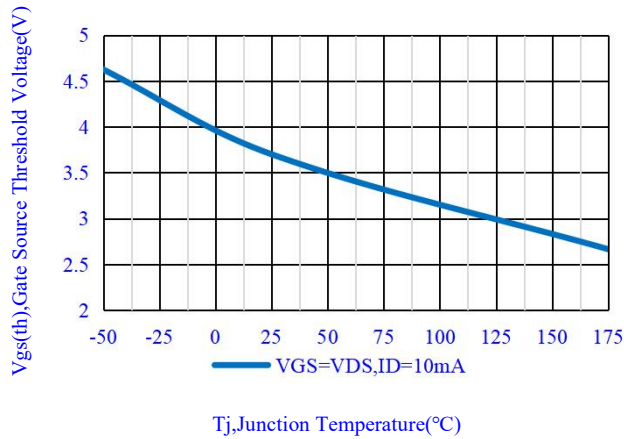


Fig.7-Gate Source Threshold Voltage Vs. Junction Temperature

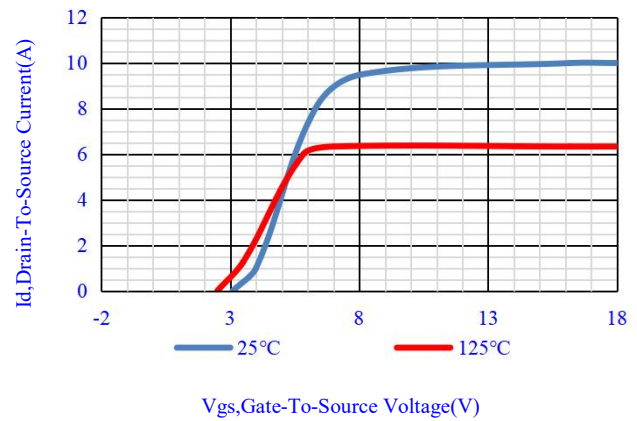


Fig.8-Transfer Characteristics

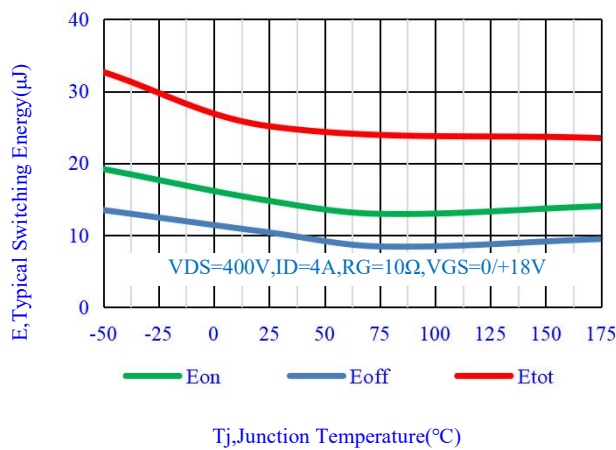


Fig.9-Typical Switching Energy Vs. Junction Temperature

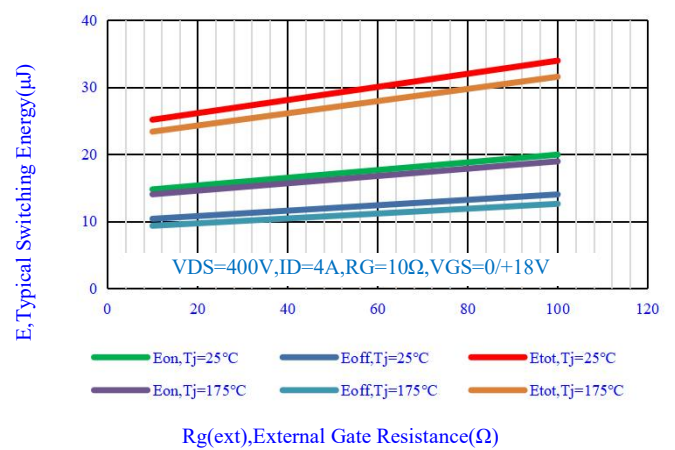


Fig.10-Typical Switching Energy Vs. External Gate Resistance

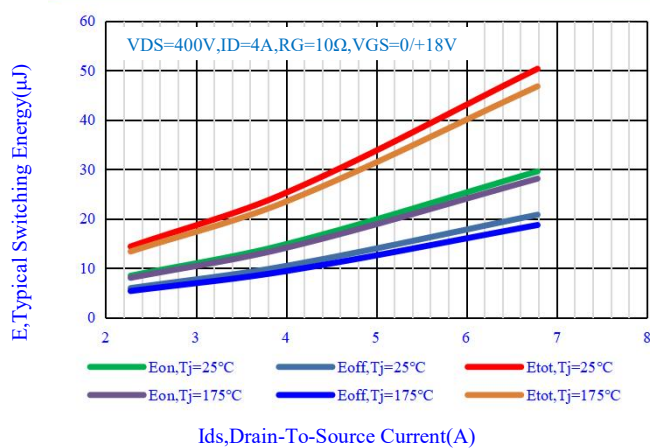


Fig.11-Typical Switching Energy Vs. Drain Source Current

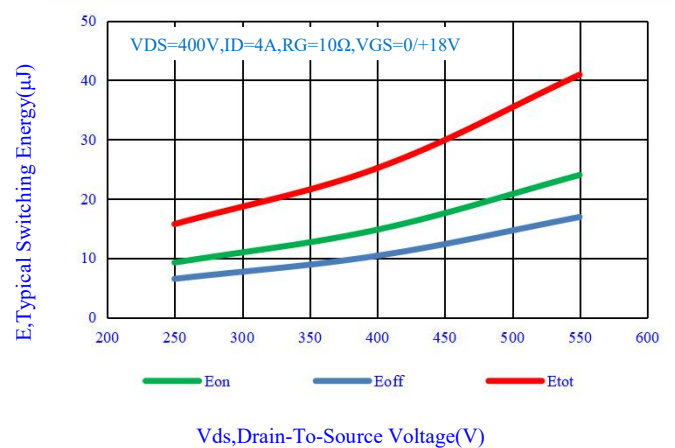


Fig.12-Typical Switching Energy Vs. Drain Source Voltage

NCH75R260F

N-Channel Silicon Carbide MOSFET



Typical Characteristics Curves

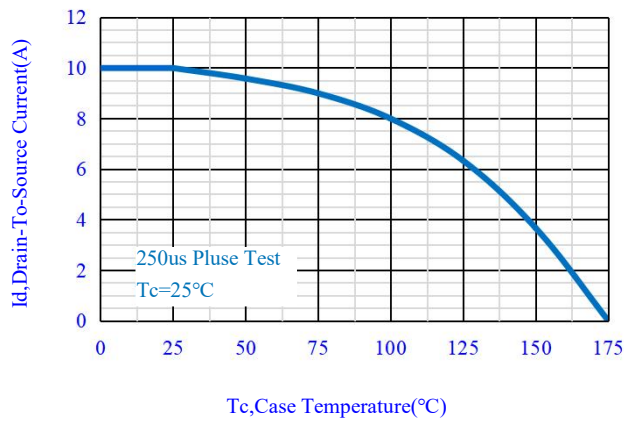


Fig.13-Maximum Continuous Drain Current Vs. Case Temperature

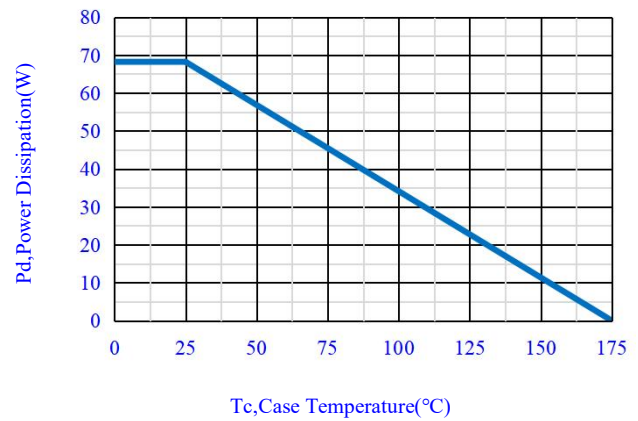


Fig.14-Maximum Power Dissipation Vs. Case Temperature

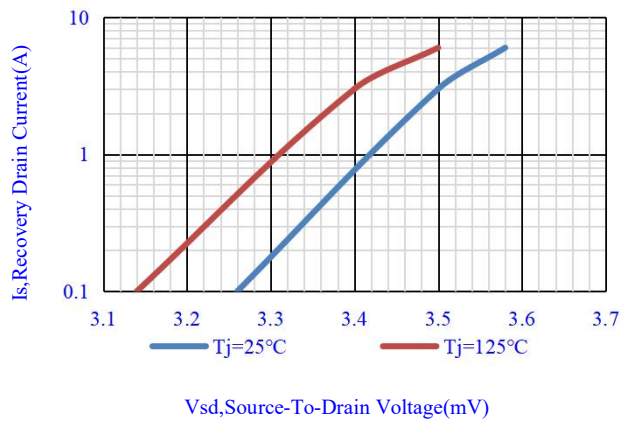


Fig.15-Source-To-Drain Diode Forward Voltage

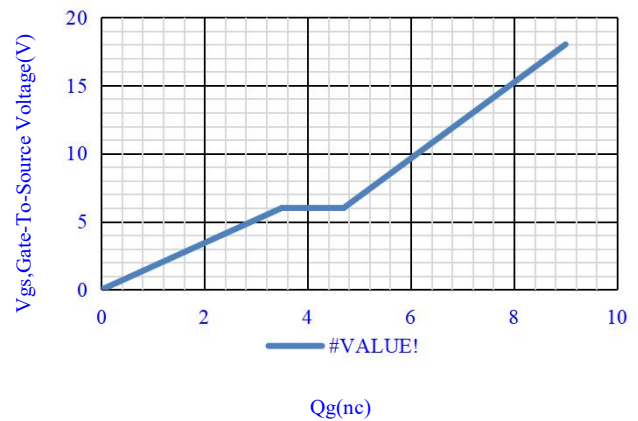


Fig.16-Gate Charge Waveform

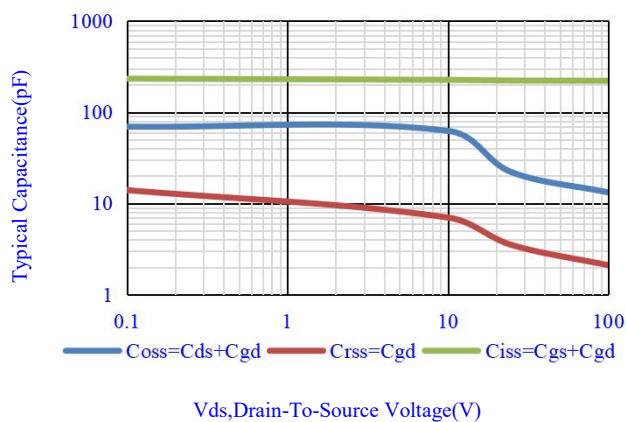


Fig.17-Typical Capacitance Vs. Drain-To-Source Voltage

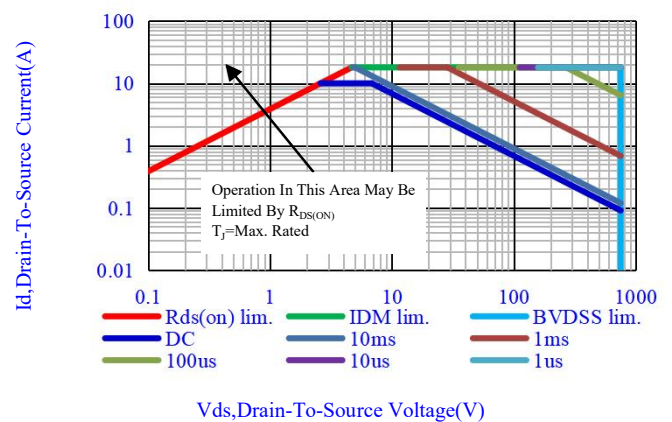


Fig.18-Maximum Safe Operating Area(SOA)

NCH75R260F

N-Channel Silicon Carbide MOSFET



Typical Characteristics Curves

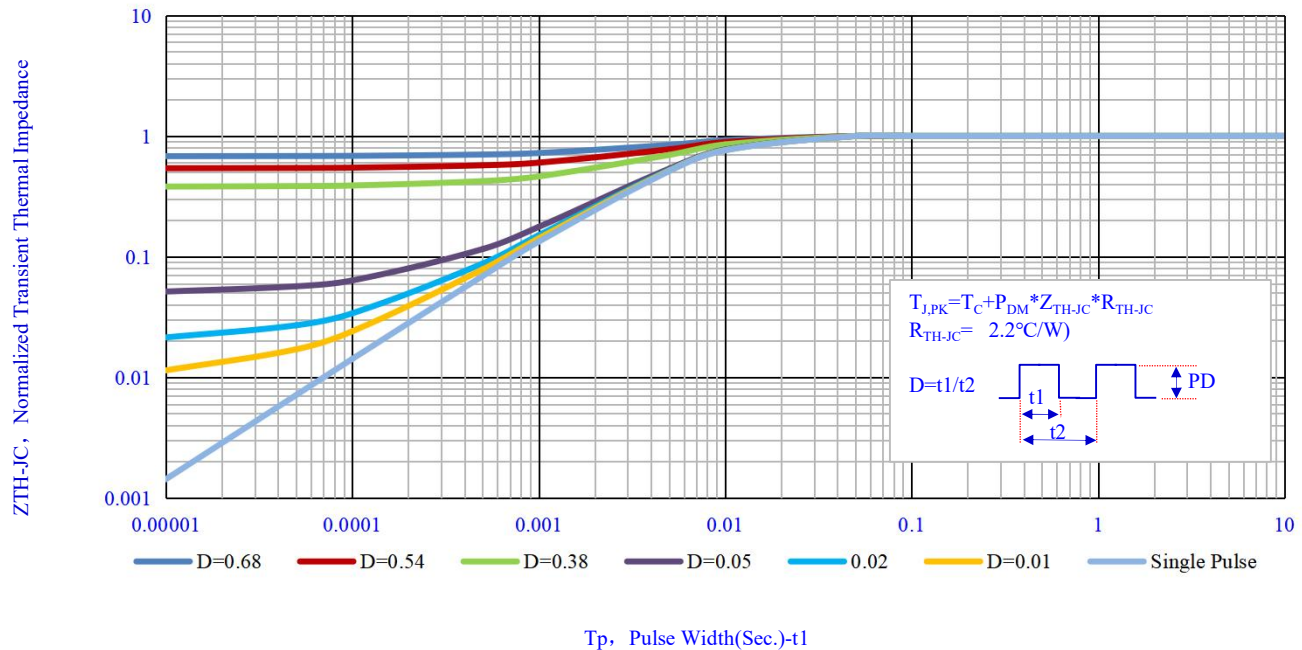


Fig.19- Normalized Maximum Transient Thermal Impedance Vs.Pulse Width

Test Circuit & Waveform

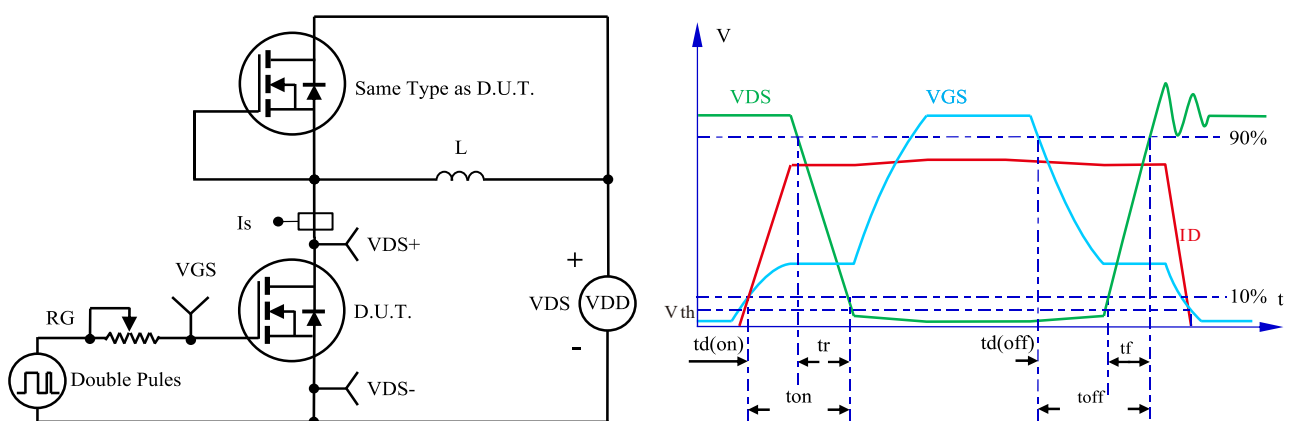


Fig.20- Inductive Switching Test Circuit & Waveform

Test Circuit & Waveform

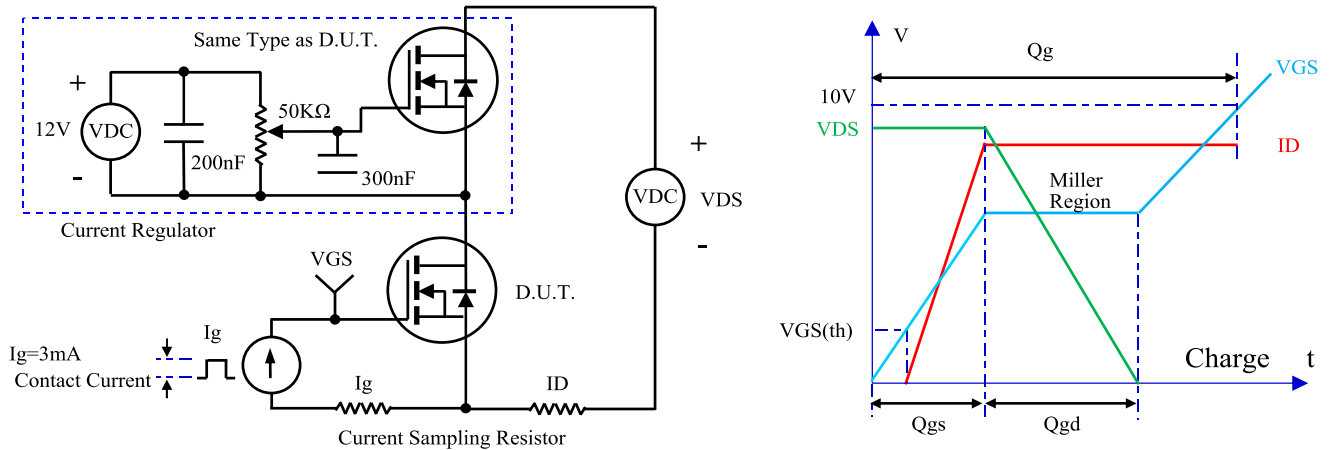


Fig.21-Gate Charge Test Circuit & Waveform

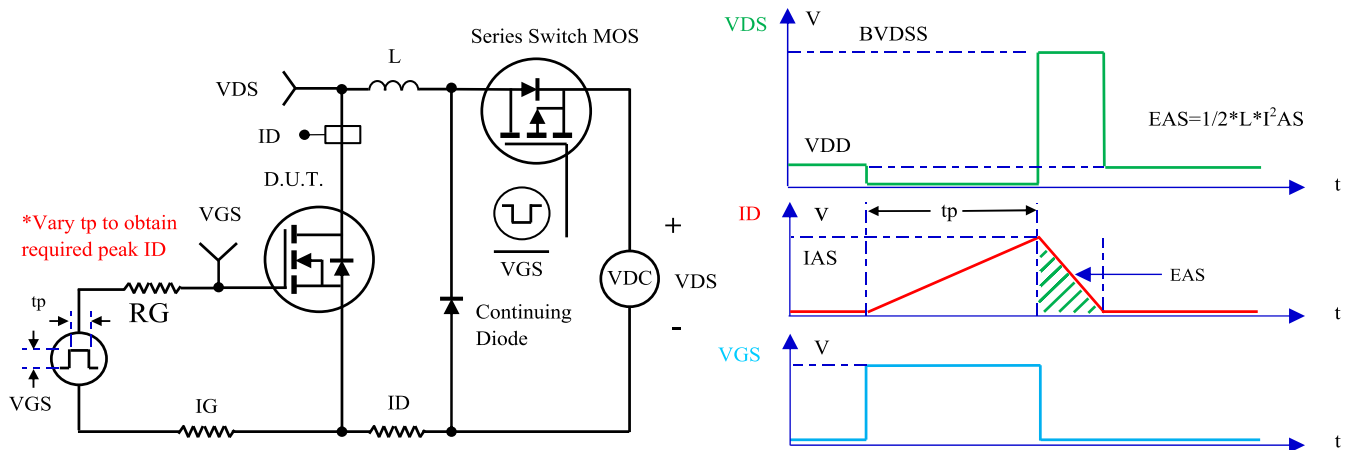


Fig.22- Unclamped Inductive Switching (UIS) Test Circuit & Waveform

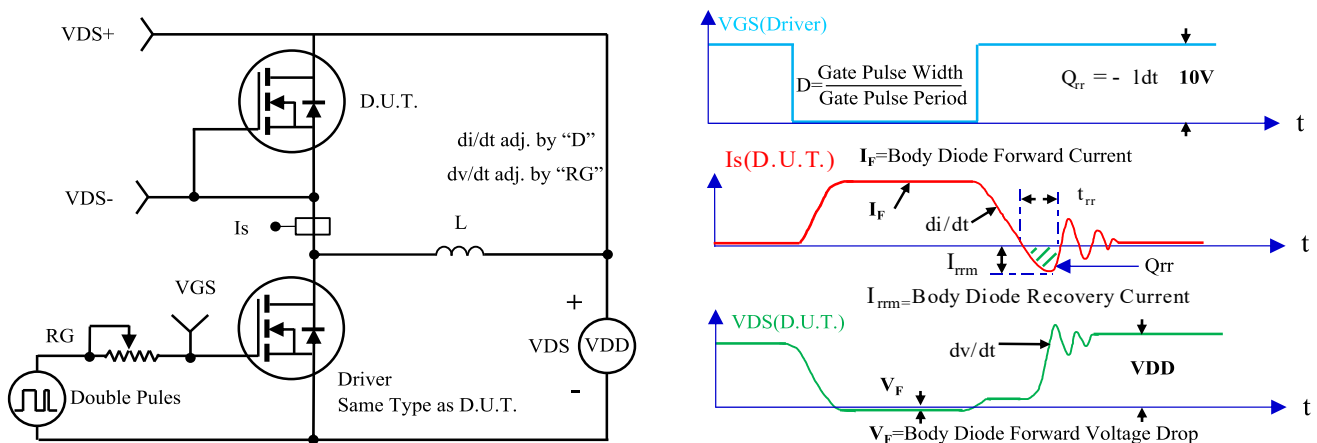


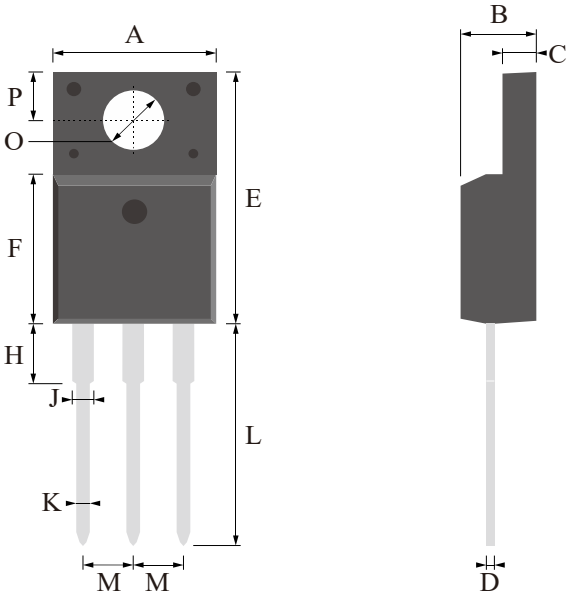
Fig.23- Diode Recovery Test Circuit & Waveform

NCH75R260F

N-Channel Silicon Carbide MOSFET



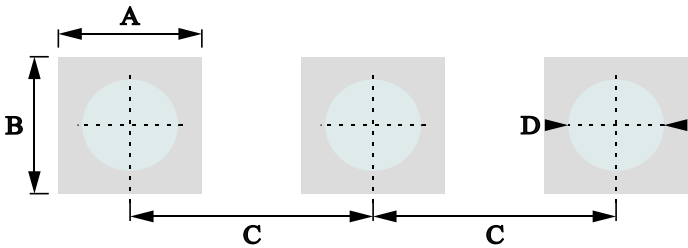
OUTLINE DRAWINGS



TO-220FP

OUTLINE DIMENSIONS						
Dim.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.25	-	10.75	0.3642	-	0.4232
B	4.20	-	5.20	0.1654	-	0.2047
C	2.30	-	2.90	0.0906	-	0.1142
D	0.35	-	0.75	0.0138	-	0.0295
E	14.80	-	16.80	0.5827	-	0.6614
F	8.25	-	9.75	0.3248	-	0.3839
L	12.15	-	14.15	0.4783	-	0.5571
H	2.60	-	3.30	0.1024	-	0.1299
J	1.10	-	1.60	0.0433	-	0.0630
K	0.60	-	1.00	0.0236	-	0.0394
M	2.20	-	3.00	0.0866	-	0.1181
O	2.70	-	3.50	0.1063	-	0.1378
P	3.20	-	3.80	0.1260	-	0.1496

RECOMMEDND LAYOUT DRAWINGS



TO-220FP

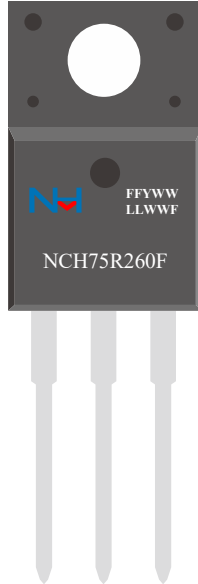
OUTLINE DIMENSIONS						
Dim.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	1.60	-	-	0.0630	-
B	-	1.60	-	-	0.0630	-
C	-	2.54	-	-	0.1000	-
D	-	1.00	-	-	0.0394	-

NCH75R260F

N-Channel Silicon Carbide MOSFET



MARKING INFORMATION



MARKING INSTRUCTIONS

NH=Niuhan Trademark
FF=Product Line Code,According To Actual Changes
YWW=Date Code,According To Actual Changes
LLWWF=Internal Code,According To Actual Changes
NCH75R260F=Model

PACKING INFORMATION

Package Type	Package Code	Product Weight Approx(g/Pcs)	Package Method	Quantity (Pcs/Min. Pack.)	Quantity (Pcs/Inner Box)	Quantity (Pcs/Carton)
TO-220FP	P1	2.048	Tube	50	1000	5000

NCH75R260F

N-Channel Silicon Carbide MOSFET



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow

	Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
	Average ramp-up rate (T _{Smax} to T _P)	3°C/second max.	3°C/second max.
	Preheat-Temperature Min (T _S min) -Temperature Max (T _S max) -Time(t _S min to t _S max)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
	Time maintained above: -Temperature (T _L) - Time (t _L)	183°C 60-150 seconds	217°C 60-150 seconds
	Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
	Time within 5°C of actual peak temperature (t _p)	10-30 seconds	20-40 seconds
	Ramp down rate	6°C/second max.	6°C/second max.
	Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

Disclaimer

- Reproducing and modifying information of the document is prohibited without permission from Niuhan Electronics Technology Co., LTD
- Niuhan Electronics Technology Co., LTD. reserves the rights to make changes of the content herein the document anytime without notification.
- Niuhan Electronics Technology Co., LTD. disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- Niuhan Electronics Technology Co., LTD. does not assume any and all implied warranties,including warranties of fitness for particular purpose,non-infringement and merchantability.
- Applications shown on the herein document are examples of standard use and operation.Customers are responsible in comprehending the suitable use in particular applications.Niuhan Electronics Technology Co., LTD.makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.
- The products shown herein are not designed and authorized for equipments requiring high level of reliability or relating to human life and for any applications concerning life-saving or life-sustaining,such as medical instruments.transportation equipment,aerospace machinery et cetera.Customers use or selling these products for use in such applications do so at their own risk and agree to fully indemnify Niuhan Electronics Technology Co., LTD.for any damages resulting from such improper use or sale.
- When the appearance of the product and chip size does not change, in order to product the customer. quality, change the internal structure and the production process Niuhan can not notify

NCH75R260F

N-Channel Silicon Carbide MOSFET



Specification Revision History

Rev.	Date	Changed Items	Pre-Changed Content	Changed Content
A/1	2025-10-20	First Issue		
		Blank Below		